

60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-1.9 A

Features

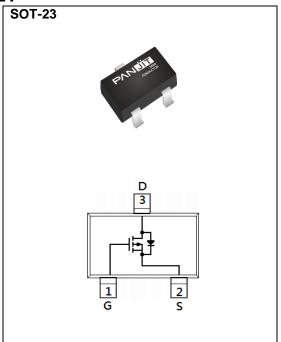
- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_{D}@-1.9A<200m\Omega$
- $R_{DS(ON)}$, V_{GS} @-4.5V, I_D @-1.5A<270m Ω
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: SOT-23 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0084 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	-60	_ v	
Gate-Source Voltage		V _{GS}	±20		
Continuous Drain Current(Note 3)	T _A =25°C	l _D	-1.9		
	T _A =70°C		-1.6	Α	
Pulsed Drain Current(Note 1)	T _A =25°C	I _{DM}	-7.6		
Power Dissipation	T _A =25°C	Б	1.5	W	
	T _A =70°C	PD	1.05		
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C	
Thermal Resistance(Note 3,4)	Junction to Ambient	$R_{\theta JA}$	100	°C/W	



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-60	-	-	\ \	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.7	-2.5		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-1.9A	-	160	200	0	
		V _{GS} =-4.5V, I _D =-1.5A	o=-1.5A - 204		270	mΩ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V	-	-	-1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic ^(Note 5)							
Total Gate Charge	Q_g		-	9	13	nC	
Gate-Source Charge	Q_{gs}	V _{DS} =-30V, I _D =-1.9A, V _{GS} =-10V ^(Note 2)	-	1.5	-		
Gate-Drain Charge	Q_{gd}	VGS=-10V(Note 2)	-	1.5	-		
Input Capacitance	Ciss		-	340	510	pF	
Output Capacitance	Coss	V _{DS} =-30V, V _{GS} =0V,	-	27	50		
Reverse Transfer Capacitance	Crss	f=1MHz	-	17	30		
Gate resistance	Rg	f=1MHz	-	14.4	-	Ω	
Turn-On Delay Time	td _(on)	.,	-	3.6	-		
Turn-On Rise Time	tr	V _{DS} =-30V, I _D =-1.9A,	-	2.9	-		
Turn-Off Delay Time	td _(off)	V _{GS} =-10V,	-	19	-	ns	
Turn-Off Fall Time	tf	$R_G=6\Omega^{(Note\ 1,2)}$	-	8	-		
Drain-Source Diode	•		•			•	
Diode Forward Current	Is	T _c =25°C	-	-	-1.9	A	
Pulsed Diode Forward Current	I _{SM}	Tc=25 C	-	-	-7.6		
Diode Forward Voltage	V _{SD}	Is=-1A, V _{GS} =0V	-	-0.8	-1	V	
Reverse Recovery Time	Trr	V _{DD} =-30V,V _{GS} =0V,	-	9	-	ns	
Reverse Recovery Charge	Qrr	I _S =-1.9A,dI _S /dt=100A/us	-	5	-	nC	

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an $R_{\theta JA}=100$ °C/W.
- 4. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

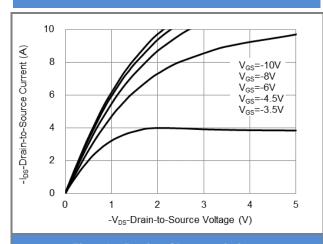


Fig.1 On-Region Characteristics

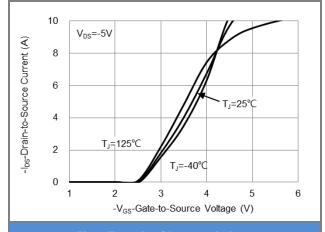


Fig.2 Transfer Characteristics

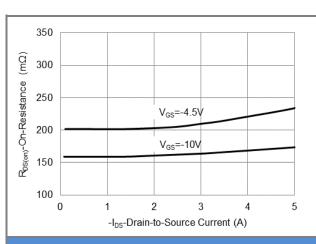


Fig.3 On-Resistance vs. Drain Current

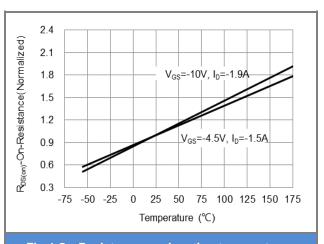
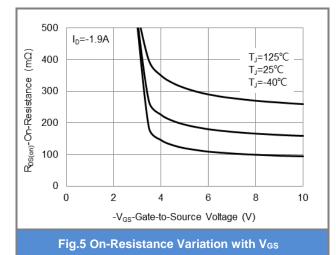


Fig.4 On-Resistance vs. Junction temperature



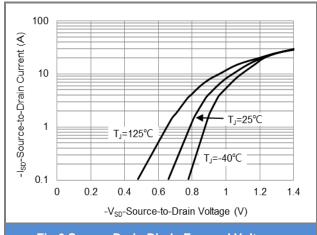


Fig.6 Source-Drain Diode Forward Voltage



TYPICAL CHARACTERISTIC CURVES

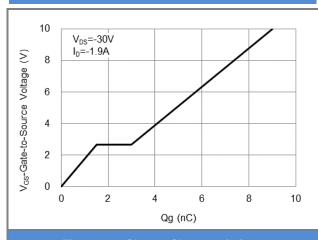


Fig.7 Gate-Charge Characteristics

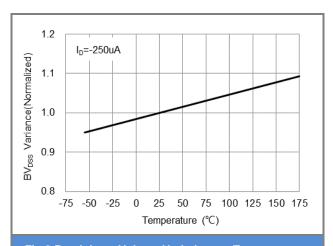


Fig.8 Breakdown Voltage Variation vs. Temperature

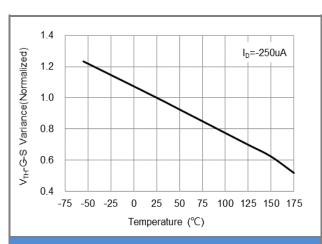


Fig.9 Threshold Voltage Variation with Temperature

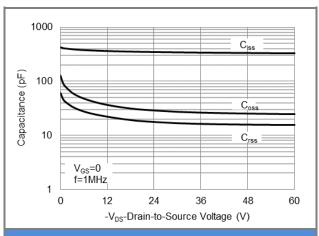
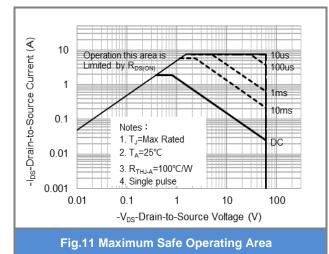
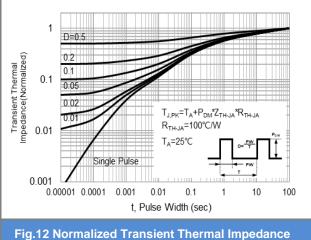


Fig.10 Capacitance vs. Drain-Source Voltage



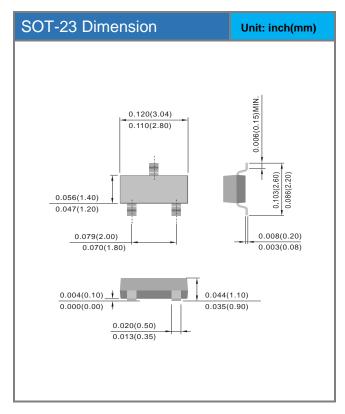


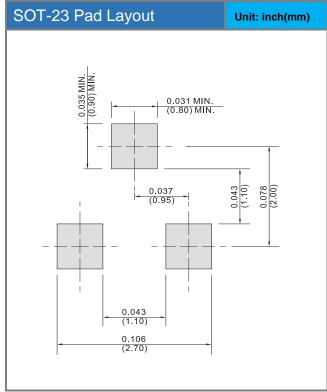


Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJA3461S-AU	SOT-23	3K pcs / 7" reel	61S	

Packaging Information & Mounting Pad Layout







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